Ordering number:ENN6385

P-Channel Silicon MOSFET

3LP02C

Ultrahigh-Speed Switching Applications

Features

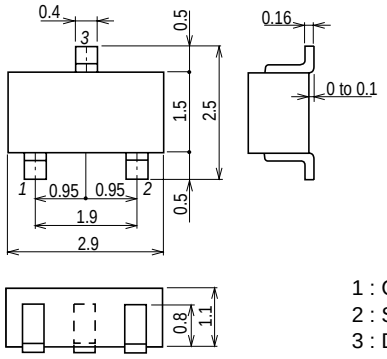
- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit:mm

2091A

[3LP02C]



1 : Gate
2 : Source
3 : Drain
SANYO : CP

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		–30	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		–0.2	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	–0.8	A
Allowable Power Dissipation	P_D		0.25	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=–1mA, V_{GS}=0	–30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=–30V, V_{GS}=0			–10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=–10V, I_D=–100μA	–0.4		–1.4	V
Forward Transfer Admittance	| yfs |	V_{DS}=–10V, I_D=–100mA	0.21	0.3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}1$	I_D=–100mA, V_{GS}=–4V		2.4	3.1	Ω
	$R_{DS(on)}2$	I_D=–50mA, V_{GS}=–2.5V		3.5	4.9	Ω
	$R_{DS(on)}3$	I_D=–10mA, V_{GS}=–1.5V		10	20	Ω

Marking : XD

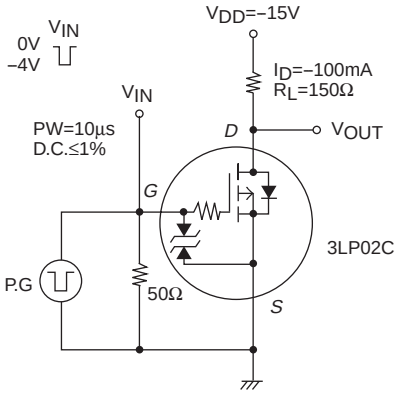
Continued on next page.

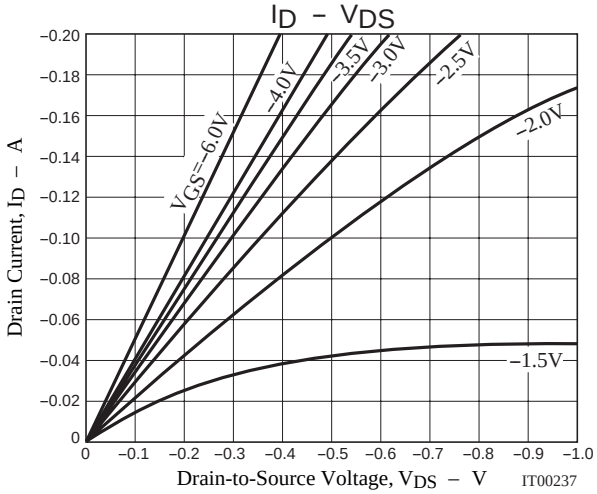
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

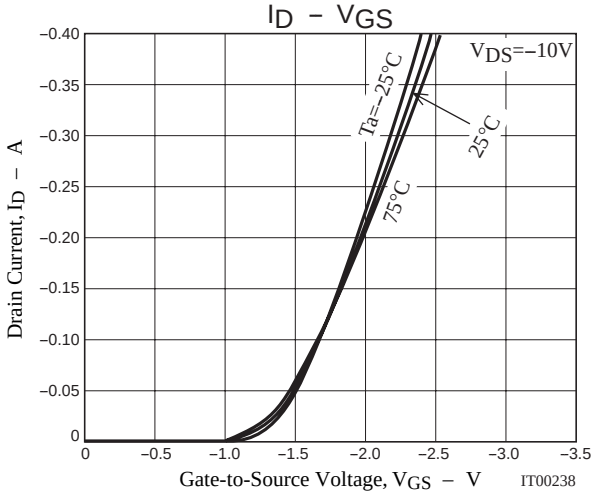
Continued from preceding page.

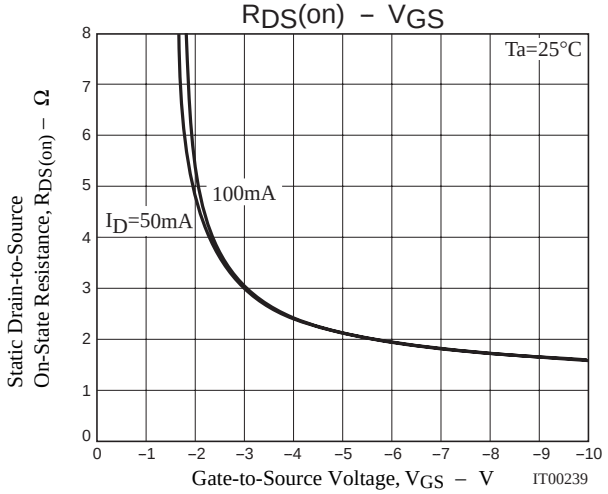
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		28		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		5.2		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		24		ns
Rise Time	t_r	See specified Test Circuit		75		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		200		ns
Fall Time	t_f	See specified Test Circuit		150		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=–10V, I_D=–200mA		2		nC
Gate-to-Source Charge	Qgs	V_{DS}=–10V, V_{GS}=–10V, I_D=–200mA		0.25		nC
Gate-to-Drain "Miller" Charge	Qgd	V_{DS}=–10V, V_{GS}=–10V, I_D=–200mA		0.35		nC
Diode Forward Voltage	V_{SD}	I_S=–200mA, V_{GS}=0		–0.82	–1.2	V

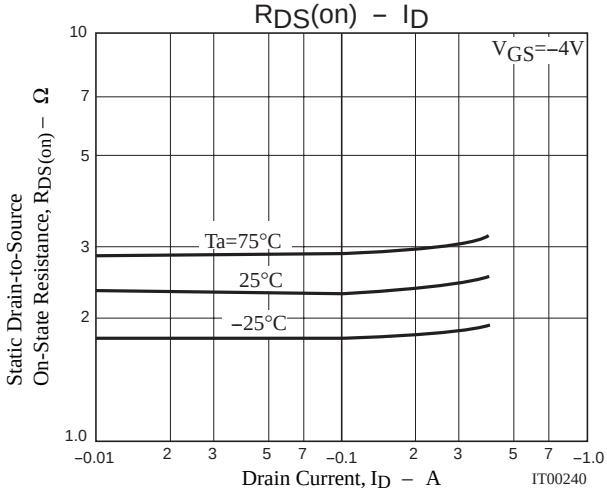
Switching Time Test Circuit

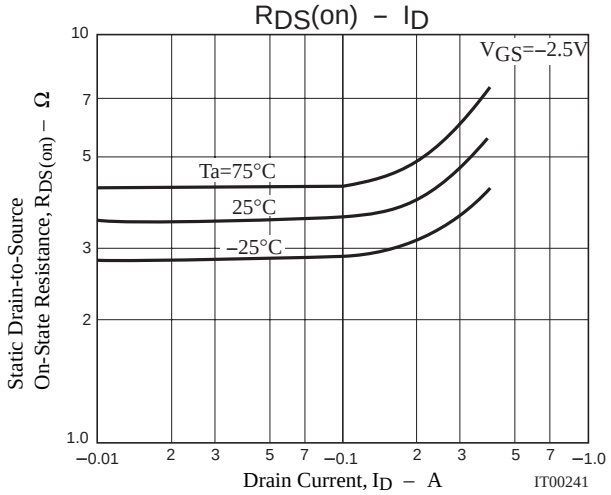


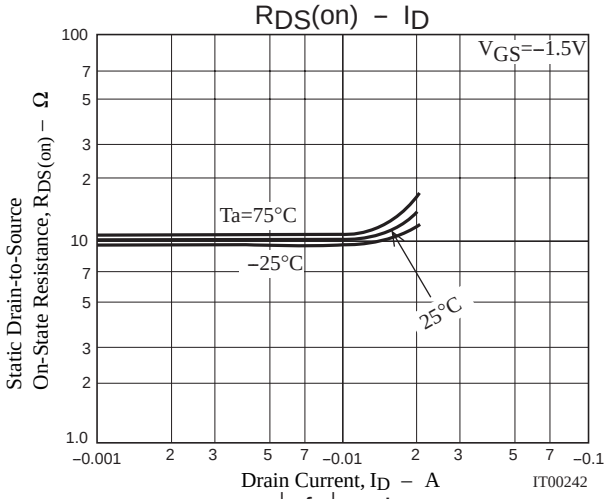


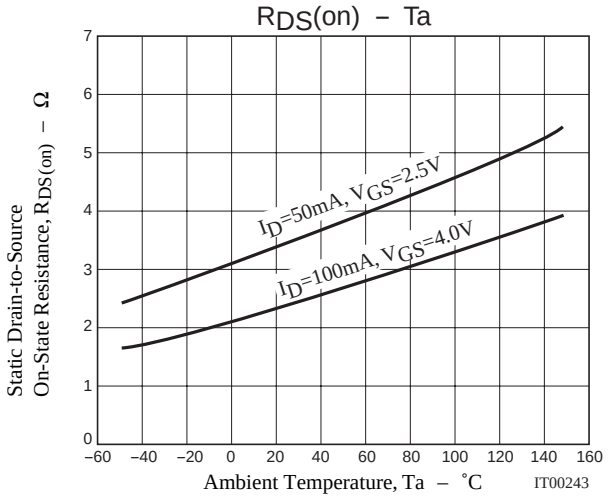


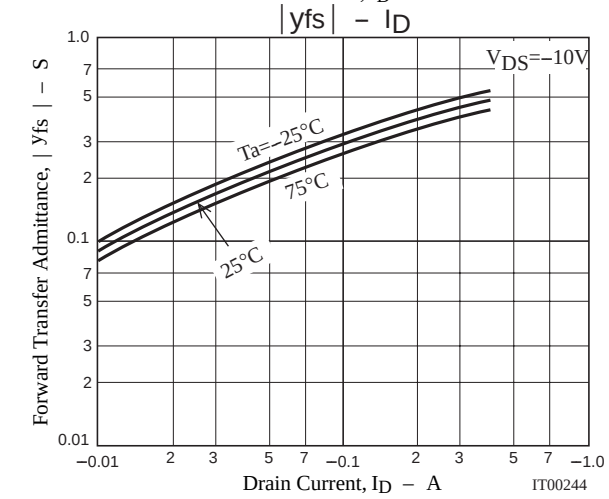


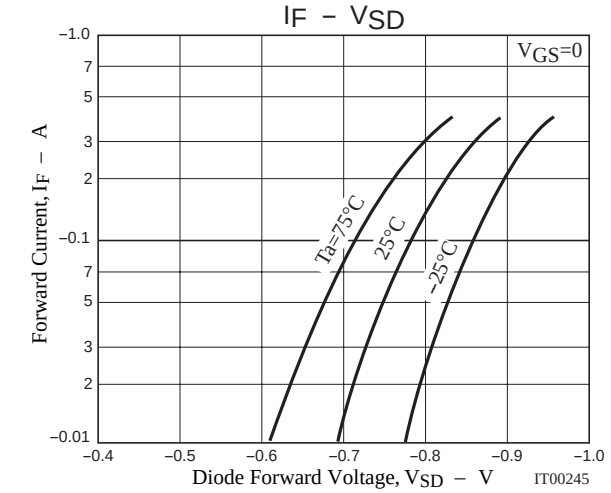


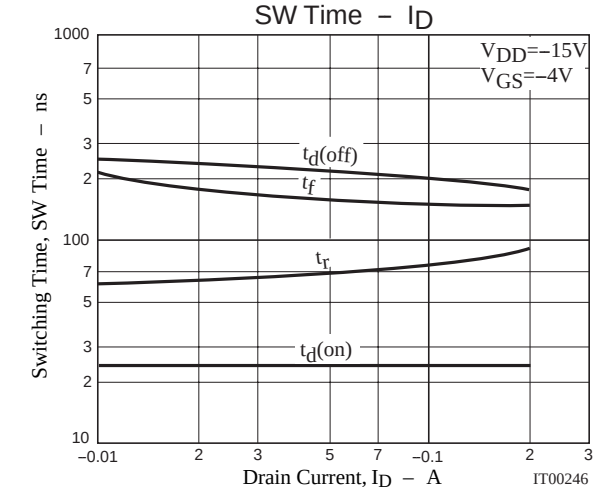

RDS(on) – ID
VGS=–2.5V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00241

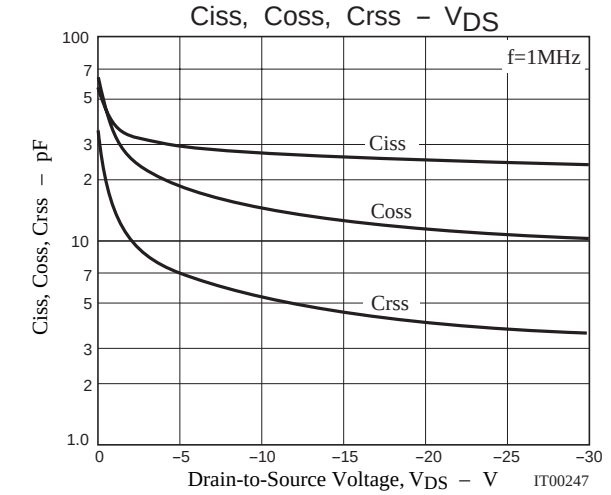

RDS(on) – ID
VGS=–1.5V
Ta=75°C
–25°C
25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00242

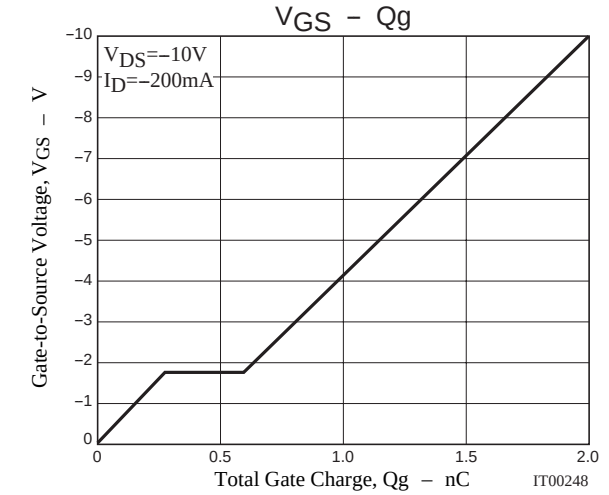

RDS(on) – Ta
ID=50mA, VGS=2.5V
ID=100mA, VGS=4.0V
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Ambient Temperature, Ta – °C
IT00243


|yfs| – ID
VDS=–10V
Ta=–25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT00244


IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT00245


SW Time – ID
VDD=–15V
VGS=–4V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT00246


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT00247


VGS – Qg
VDS=–10V
ID=–200mA
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT00248